

Electrical Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 2.1	1.8 2.4	V	$I_{F} = 8 \text{ A } T_{J} = 25^{\circ}\text{C}$ $I_{F} = 8 \text{ A } T_{J} = 175^{\circ}\text{C}$	Fig. 1
I _R	Reverse Current	8.5 17	42.5 170	μA	$V_{R} = 600 V T_{J} = 25^{\circ}C$ $V_{R} = 600 V T_{J} = 175^{\circ}C$	Fig. 2
Q _c	Total Capacitive Charge	20		nC	$V_{R} = 400 V, I_{F} = 8A$ $di/dt = 500 A/\mu s$ $T_{J} = 25^{\circ}C$	Fig. 5
С	Total Capacitance	395 37 32		pF	$V_{R} = 0 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 200 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 400 V, T_{J} = 25^{\circ}C, f = 1 MHz$	Fig. 6
E _c	Capacitance Stored Energy	3.0		μJ	V _R = 400 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Syr	mbol	Parameter	Тур.	Unit	Note
F	$R_{_{ ext{ heta}JC}}$	Thermal Resistance from Junction to Case	1.4	°C/W	Fig. 9

Typical Performance

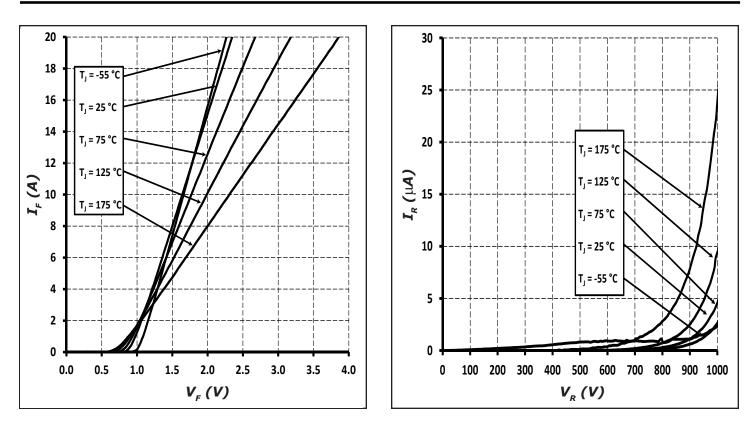
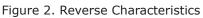


Figure 1. Forward Characteristics





Typical Performance

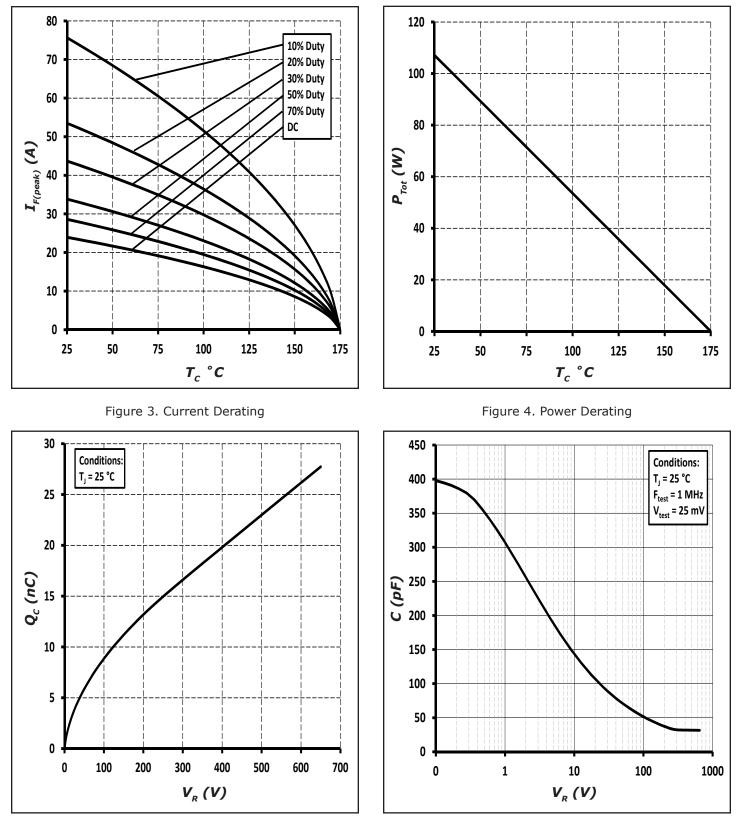
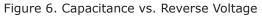


Figure 5. Total Capacitance Charge vs. Reverse Voltage



3



Typical Performance

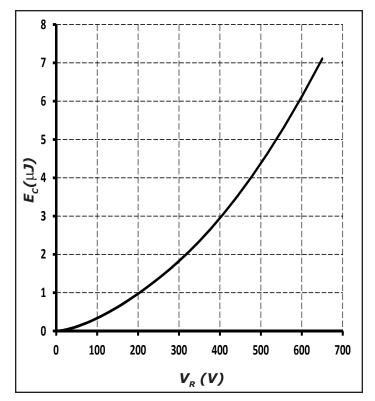


Figure 7. Capacitance Stored Energy

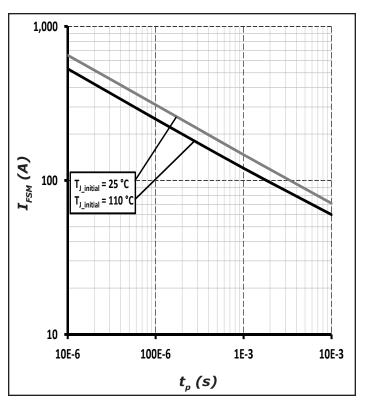


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

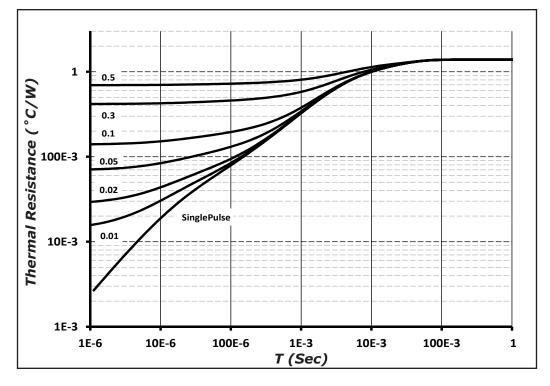
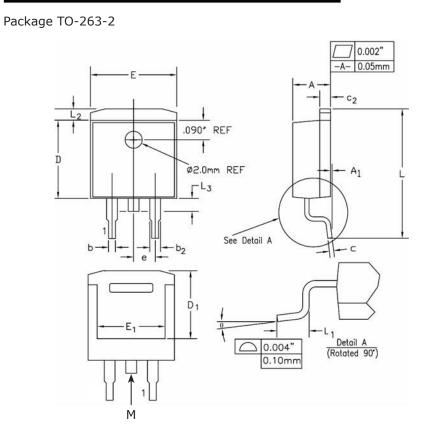


Figure 9. Transient Thermal Impedance

4

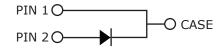


Package Dimensions

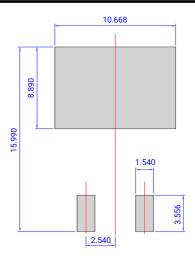


POS	Inc	hes	Millimeters		
P05	Min	Max	Min	Max	
А	0.17	0.18	4.32	4.57	
A1	-	0.01	-	0.25	
b	0.028	0.037	0.71	0.94	
b2	0.045	0.055	1.15	1.4	
с	0.014	0.025	0.356	0.635	
c2	0.048	0.055	1.22	1.4	
D	0.35	0.37	8.89	9.4	
D1	0.255	0.324	6.48	8.23	
E	0.395	0.405	10.04	10.28	
E1	0.31	0.318	7.88	8.08	
е	0.1	BSC.	2.54	BSC.	
L	0.58	0.62	14.73	15.75	
L1	0.09	0.11	2.29	2.79	
L2	0.045	0.055	1.15	1.39	
L3	0.05	0.07	1.27	1.77	
θ	0°	8°	0°	8°	

Note: Tab "M" may not be present



Recommended Solder Pad Layout



TO-263-2

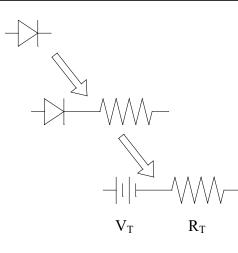
Part Number	Package	Marking		
C3D08060G	TO-263-2	C3D08060		

Note: Recommended soldering profiles can be found in the applications note here: http://www.wolfspeed.com/power_app_notes/soldering





Diode Model



 $Vf_T = V_T + If^*R_T$

$$V_{T} = 0.95 + (T_{J}^{*} - 1.2^{*}10^{-3})$$

 $R_{T} = 0.054 + (T_{J}^{*} 5.5^{*}10^{-4})$

Note: T_j = Diode Junction Temperature In Degrees Celsius valid from 25°C to 175°C

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Ecology section of our website at http://www.wolfspeed.com/Power/Tools-and-Support/Product-Ecology.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body
nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited
to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical
equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.wolfspeed.com/Power/Products#SiCSchottkyDiodes
- Schottky diode Spice models: http://www.wolfspeed.com/power/tools-and-support/DIODE-model-request2
- SiC MOSFET and diode reference designs: http://go.pardot.com/l/101562/2015-07-31/349i

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